Development of Diamond Detectors for ToF measurements at the Super-FRS

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The Super-FRS @ FAIR

Detector requirements for the Super-FRS

Diamond detectors: results so far and future beam tests

Summary

The Super-FRS @ FAIR

FAIR: Facility for Antiproton and Ion Research



The NUSTAR facility @ FAIR



Layout and design parameter of the Super-FRS



Martin Winkler, Annual NuSTAR Meeting, GSI, March.3-5, 2010

Detector requirements for the Super-FRS



Increasing in the intensity of radioactive beams

It requires new developments in detecting system & electronics

Clean full PID on event-by-event basis

- \rightarrow momentum tagging $\Delta x \sim 1$ mm
- \rightarrow ToF measurements Δ ToF ~ 100ps (FWHM)

Detector resolution



Layout of the Super-FRS beam line



Diamond detectors: current developments and future beam tests

ToF focal plane detectors

Radiation hard detector: diamond, silicon

- 4 units
- time resolution σ <50 ps
- active area 380/200mm x 50mm
- max rate 500 Hz/mm²
- fast and multi-channel integrated FEE electronics

Example: <u>pcCVD-DD</u>, (200 x 40) mm², 20 units 20x20x0.3 mm, 50 strips/units

1000 channels!!!

•100 days operation @1MHz 1.08x10¹¹ ions/cm²

Absorbed dose = 4.36×10^5 Gy ²³⁸U@350 MeV/u

Radiation hardness study with Au beam - amplitude reduction



Analog signals, Au beam, HV: 100V, Amplitude: 94 mV15/01/2014 2nd A

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TODD experiment (2012)

C beam@80MeV/u at LNS





pcCVD-DD 10x10x0.2 1 mm



- digital waveform sampled (20 GS/s scope)
- small charge collection Q=2.46pC
- M. Träger GSI-DL



The role of capacitance



Strip area: 90, 50, 12 and 6 mm² -> 14.6, 8.1, 2.0 and 1.0 pF)

(*) Type 2: commercial detector based on DLC electrodes

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Electronics with ToT capability

• PADI4 ASIC 0.18 μm CMOS

- rise time < 500 ps
- 30 fC <Q< 2000 fC
- $\sigma_{tE} < 15 \text{ ps}$
- LVDS digital outputs
- 350 MHz bandwidth





- VFTX (28 chs) VME FPGA TDC
 - LVDS inputs
 - 200 MHz clock
 - $\sigma_t < 10 \text{ ps}$

M. Ciobanu GSI-DL J. Fruehauf GSI-EE

VFTX + PADI results







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VFTX calibration

If the hit distribution in the histogram, their total number *N* and the period of the counter clock is known, the real bin width (in ps) can be calculated as:

$$W_i(\text{ps}) = \frac{N_i \cdot 5000(\text{ps})}{N}$$
 (for a 200 MHz system clock).

The corresponding time of a bin is then derived as follows:

$$T_{i} = \sum_{k=1}^{i-1} W_{k} + \frac{W_{i}}{2}$$

Expected (2014) radiation hardness tests

Where	Isotope	Energy (GeV/u)	Intensity (p/s)
Dubna	²⁰ Ne	0.054	107
Catania	¹² C	0.062	10 ⁹
GSI	²³⁸ U / ¹⁹⁷ Au	0.35 - 1.0	10 ⁶

In Dubna, are expected signals 20 mV in amplitude for the Si detectors. Considering the lower CCE for the pcCVD it is foreseen to have 5 mV signals.

Looking at the previous results for 5 mV signal and considering a threshold of 320 mV, the achievable resolution is expected to be 30 ps. It is very promising!

Such tests will also allow to understand the effects on the radiation hardness according to the different type of isotope used to irradiated the diamond samples.



pcCVD -DD 20x20x0.3 mm





Detector processing:

- Electrode metallization with Cr/Au with thickness 50/100 nm
- Photolithography by laser followed by etching
- 8 strips (1 mm) + 16 strips (0.5 mm) Gap 60 μm
- Annealing of the device at 500° in Ar



IV Characteristics sample 2340622-13



Summary

The new facility FAIR will be able to provide beams with high intensity and energy which requires new developments in detecting system & electronics.

For a clean full particle identification, detectors having spatial and timing resolution of $\Delta x \sim 1$ mm and Δ ToF ~ 100 ps (FWHM) are required.

At the Super-FRS, 4 radiation detector units (1 START + 3 STOP) should be installed with total active area of 380/200mm x 50mm.

Detectors based on diamond samples are a possible solution (not the only one!): first tests performed on diamond samples have shown the capability of the material to withstand the expected beam intensities at the Super-FRS.

First tests on the electronics are also very promising.

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Characteristics of Diamond vs Silicon

- Wider bandgap energy cooling not needed
- Larger carrier mobility stronger E field
- Fast signal collection typical rise-time ~ 100 ps
- Radiation hardness and no doping
- Low noise (in principle) low dielectric constant ($\varepsilon_r = 5.7$) – low capacitance

	Silicon	Diamond
Bandgap Energy $E_g(eV)$	1.13	5.47
e- h Prod. Energy(eV)	3.6	12.84
e^{-} Mobility(cm ² /Vs)	1500	2200
h^+ Mobility(cm ² /Vs)	600	1600
Breakdown Volt.(V/cm)	$3 imes 10^5$	10^{7}

Back

Diamond detectors

borrowed from GSI detector lab

PCCVD monitor (D1)

size (10x10) mm² , 600 μ m thickness Cr-Au metallization (200 nm)

V = -/+ 600 Volts



9 strips PCCVD detector (D2)

size (30x30) mm², 360 μ m thickness, 9 strips (3 mm pitch)

Ti-Au electrods (200nm)

V = -/+ 400 Volts

C = 10 pF/strip

